

In the Claims:

1. (Currently Amended) Gas sensor having first and second sensor regions responding to at least one reactive exhaust gas constituent and having a catalytic agent for converting reactive exhaust gas constituents with a higher catalytic activity in said first sensor region, wherein characterized in that the first sensor region comprises pores in which traces of at least one catalytically active substance are present as the catalytic agent and further wherein the sensor regions are independent of one another and comprise a resistive semiconductor layer.
2. (Currently Amended) Gas sensor according to the preceding claim 1 wherein the second sensor region also comprises pores in which traces of at least one catalytically active substance are present, said and the concentration of catalytically active substance being is lower than in the first region layer.
3. (Currently Amended) Gas sensor according to the preceding claim 1, wherein the concentration of catalytically active substance in the second sensor region is zero.
4. (Previously Amended) Gas sensor according to claim 1, wherein a platinum metal is employed as the catalytically active material, which is produced by thermolysis of a platinum-containing compound introduced in fluid form into the pores.
5. (Cancelled)
6. (Currently Amended) Gas sensor according to claim 1, wherein the sensor region is manufactured as a thick-film semiconductor with having a silk-screened pore formation by silk screening.

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7. (Currently Amended) Gas sensor according to the preceding claim 1, wherein the sensor region is manufactured of strontium titanate.
8. (Currently Amended) Gas sensor arrangement having a gas sensor according to the preceding claim 1, which includes with a parallel evaluation circuit for parallel evaluation of the resistance values of both sensor regions.